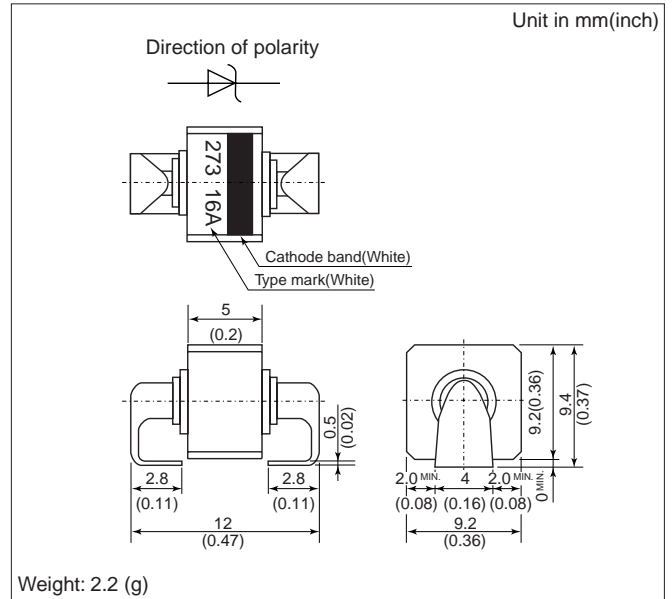


ZSA5MA27

FEATURES

- High transient reverse power capability suitable for protecting automobile electronic components etc.

OUTLINE DRAWING



ABSOLUTE MAXIMUM RATINGS

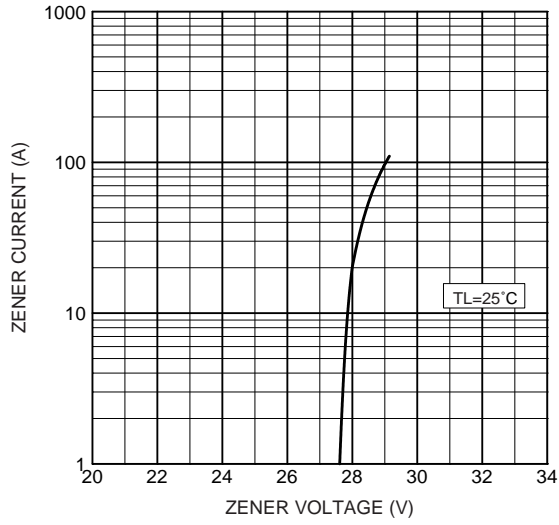
Items	Symbols	Units	Ratings
Non-Repetitive Peak Reverse One-Cycle Dissipation	P_{RSM}	W	3,000(Rectangular pulse $t=1$ ms $T_L=25^\circ\text{C}$ start)
Non-Repetitive Peak Reverse Surge Current	I_{RSM}	A	62(Time constant=14.5ms, $T_L=25^\circ\text{C}$)
DC Reverse Voltage	V_{DC}	V	18
Operating Junction Temperature	T_j	$^\circ\text{C}$	-40 ~ +150
Storage Temperature	T_{stg}	$^\circ\text{C}$	-40 ~ +150

CHARACTERISTICS($T_L=25^\circ\text{C}$)

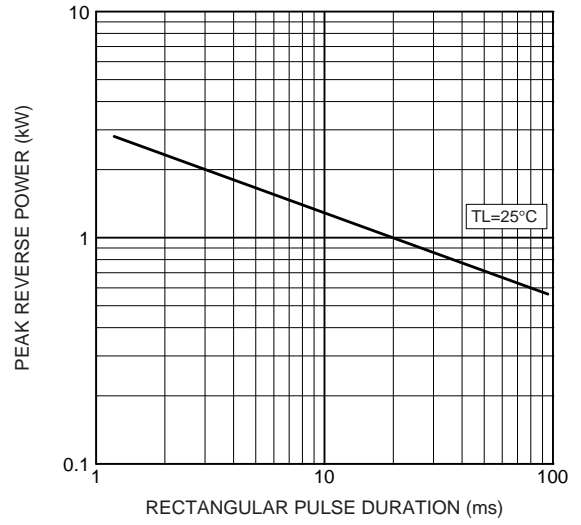
Items	Symbols	Units	Min.	Typ.	Max.	Test Conditions
Zener Voltage	V_Z	V	24	27	30	$I_Z=10$ mA
Dynamic Impedance	Z_Z	Ω	-	-	50	$I_Z=10$ mA
Zener Voltage Temperature Coefficient	γ_Z	$\%/^\circ\text{C}$	-	0.074	-	$I_Z=10$ mA
Peak Forward Voltage	V_{FM}	V	-	-	2	$I_{FM}=6$ A
Peak Reverse Current	I_{RRM}	μA	-	-	50	$V_R=18$ V

ZSA5MA27

Typical zener characteristics



Typical reverse power characteristic
(Rectangular pulse non-repetitive)



HITACHI POWER SEMICONDUCTORS

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